

Title (en)
Method for packaging and mounting semiconductor device

Title (de)
Verfahren zur Verpackung und zum Aufbau einer Halbleitervorrichtung

Title (fr)
Procédé d'emballage et de montage d'un dispositif semiconducteur

Publication
EP 1043772 A2 20001011 (EN)

Application
EP 00301898 A 20000308

Priority
JP 10259999 A 19990409

Abstract (en)
A semiconductor device in accordance with the present invention reduces cracks occurring in a junction between a semiconductor device and a mounting substrate due to a heat stress when the semiconductor device is mounted on a printed circuit board or the like. The semiconductor device has a semiconductor element having a thickness of 200 μm or less, an electrode pad formed on the semiconductor element, a post electrically connected to the electrode pad, and a sealing resin for sealing a surface where circuitry is formed and the post. Furthermore, a manufacturing method for a semiconductor device in accordance with the present invention includes a step for forming an electrode pad on a main surface of a semiconductor wafer, a step for forming a post to be connected to the electrode pad, a step for resin-sealing the main surface of the semiconductor wafer and the post, a step for forming a groove from a surface of the resin to a predetermined depth of the semiconductor wafer, and a step for polishing a rear surface of the semiconductor wafer to a bottom of the groove and dividing the semiconductor wafer into individual semiconductor devices. <IMAGE> <IMAGE> <IMAGE> <IMAGE> <IMAGE>

IPC 1-7
H01L 23/31; **H01L 23/498**

IPC 8 full level
H01L 21/301 (2006.01); **H01L 21/304** (2006.01); **H01L 21/56** (2006.01); **H01L 21/68** (2006.01); **H01L 23/02** (2006.01); **H01L 23/31** (2006.01)

CPC (source: EP KR US)
H01L 21/56 (2013.01 - EP US); **H01L 21/6835** (2013.01 - EP US); **H01L 21/6836** (2013.01 - EP US); **H01L 23/02** (2013.01 - KR); **H01L 23/3114** (2013.01 - EP US); **H01L 24/27** (2013.01 - EP US); **H01L 24/05** (2013.01 - EP); **H01L 2221/68327** (2013.01 - EP US); **H01L 2221/6834** (2013.01 - EP US); **H01L 2224/023** (2013.01 - EP); **H01L 2224/05001** (2013.01 - EP US); **H01L 2224/05008** (2013.01 - EP US); **H01L 2224/05026** (2013.01 - EP US); **H01L 2224/05569** (2013.01 - EP US); **H01L 2224/131** (2013.01 - EP US); **H01L 2224/16** (2013.01 - EP US); **H01L 2224/274** (2013.01 - EP US); **H01L 2224/94** (2013.01 - EP US); **H01L 2924/00013** (2013.01 - EP US); **H01L 2924/01029** (2013.01 - EP US); **H01L 2924/14** (2013.01 - EP US); **H01L 2924/3511** (2013.01 - EP US)

Cited by
DE10391795B4

Designated contracting state (EPC)
DE FR GB

DOCDB simple family (publication)
EP 1043772 A2 20001011; **EP 1043772 A3 20051012**; **EP 1043772 B1 20170503**; JP 2000294519 A 20001020; JP 3423245 B2 20030707; KR 100689209 B1 20070308; KR 20000076798 A 20001226; TW 452936 B 20010901; US 2003006510 A1 20030109; US 2003173658 A1 20030918; US 2004099937 A1 20040527; US 6476501 B1 20021105; US 6613694 B2 20030902; US 6680535 B2 20040120; US 7314779 B2 20080101

DOCDB simple family (application)
EP 00301898 A 20000308; JP 10259999 A 19990409; KR 20000011749 A 20000309; TW 89104578 A 20000314; US 23549402 A 20020906; US 38649003 A 20030313; US 46098799 A 19991215; US 71854903 A 20031124